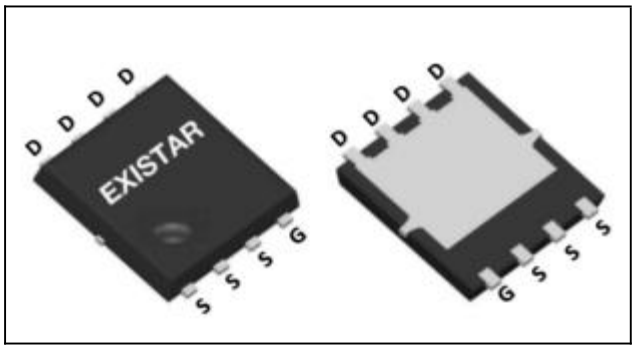
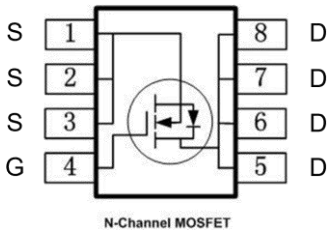
N-Channel 150V MOSFET

E150N9P0HH1

V_{DS} (V)	$R_{DS(on),typ}$ (mΩ)	I_D (A)
150V	9.0 @ V_{GS} = 10V	100

PDFN5X6





Pb-free
RoHS COMPLIANT
HALOGEN FREE

Features

- Low $R_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested

Applications

- DC/DC conversion
- Power switch
- PD charger
- Moto driver

Package And Ordering Information

Ordering code	Package	Marking
E150N9P0HH1	PDFN5x6	E150N9P0HH1

Ordering Information

Package	Units/ Reel	Reels/ Inner Box	Units/ Inner Box
PDFN5x6	5000	1	5000

Key Performance Parameters

Parameter	Value	Unit
VDS, min @ Tj(max)	150	V
ID, pulse	400	A
RDS(ON), typ @ VGS=10V	9.0	mΩ
Qg	90	nC

Absolute Maximum Ratings at Tj=25°C Unless Otherwise Noted

Parameter		Symbol	Limit	Unit
Drain-source voltage		V_{DS}	150	V
Gate-source voltage		V_{GS}	±20	
Continuous drain current	T_C=25°C	I_D	100	A
	T_C=100°C		-	
Pulsed drain current		$I_{D,pulse}$	400	
Avalanche energy, single pulse		E_{AS}	343	mJ
Power dissipation	T_C=25°C	P_D	200	W
	T_A=25°C		-	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to 175	℃

Thermal Characteristics

Parameter		Symbol	Max.	Unit
Thermal resistance, junction-to-case	Steady state	$R_{\theta JC}$	1	°C/W
Thermal resistance, junction-to-ambient	Steady state	$R_{\theta JA}$	62	

Electrical Characteristics at Tj=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Static						
Drain to source breakdown voltage	$V_{(BR)DSS}$	150			V	V_{GS} = 0, I_D = 250 μA
Gate-source threshold voltage	$V_{GS(th)}$	2.5		4.5	V	V_{DS} = V_{GS}, I_D = 250 μA
Gate-body leakage	I_{GSS}			±100	nA	V_{DS} = 0 V, V_{GS} = ±20 V
Zero gate voltage drain current	I_{DSS}			1	μA	V_{DS} = 150 V, V_{GS} = 0 V
Drain-source on-resistance	$R_{DS(on)}$		8.5	9.8	mΩ	V_{GS} = 12 V, I_D = 20 A
Drain-source on-resistance	$R_{DS(on)}$		9.2	10.5	mΩ	V_{GS} = 8 V, I_D = 15 A
Gate resistance	Rg		2.1		Ω	f=1MHz

Gate Charge						
Total gate charge	Qg		90		nC	V_{DS} = 120 V, I_D = 40 A, V_{GS} = 12 V
Gate-source charge	Qgs		17			
Gate-drain charge	Qgd		15			
Dynamic						
Turn-on delay time	$t_{d(on)}$		16		ns	V_{DS} = 120 V, I_D =40 A, V_{GS} = 12 V, R_{GEN} = 2 Ω
Rise time	t_r		15			
Turn-off delay time	$t_{d(off)}$		67			
Fall time	t_f		19			
Input capacitance	C_{iss}		5400		pF	V_{DS} =25 V, V_{GS} = 0 V, f = 1MHz
Output capacitance	C_{oss}		1645			
Reverse transfer capacitance	C_{rss}		152			
Body Diode						
Diode forward voltage	V_{SD}			1.1	V	V_{GS} = 0 V, I_F = 50 A
Reverse recovery time	t_{rr}		66		ns	V_R= 120 V, I_S =40 A, di/dt = 400 A/μs
Reverse recovery charge	Q_{rr}		443		nC	
Peak reverse recovery current	I_{rrm}		10		A	

Electrical Characteristics Diagrams

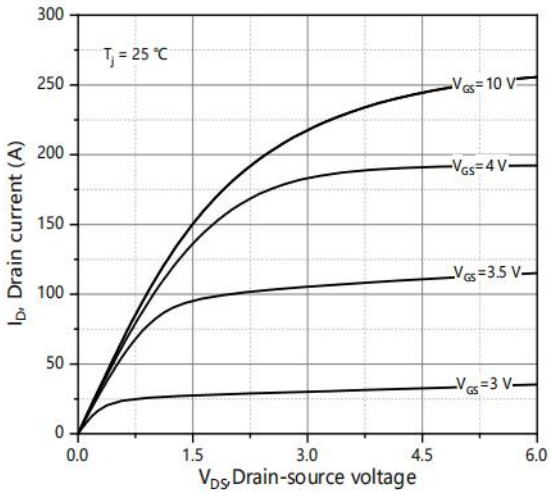


Figure 1. Typ. output characteristics

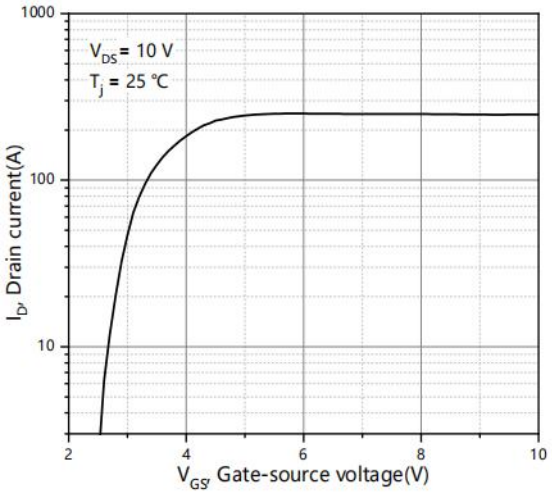


Figure 2. Typ. transfer characteristics

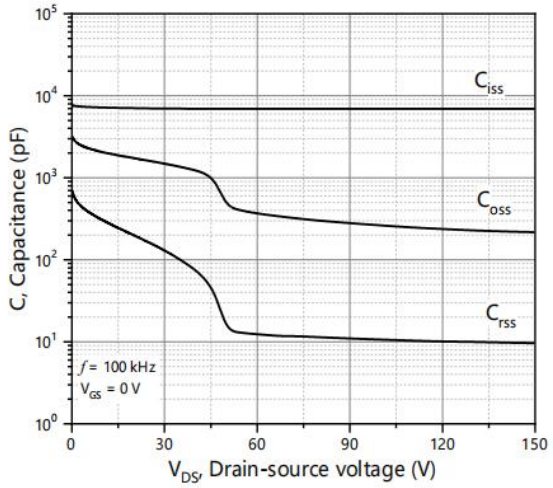


Figure 3. Typ. capacitances

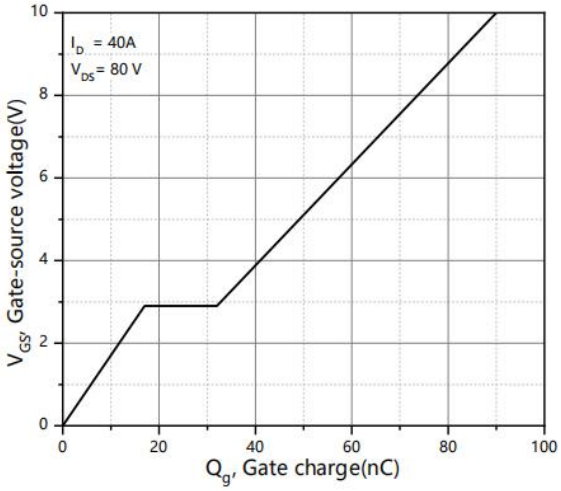


Figure 4. Typ. gate charge

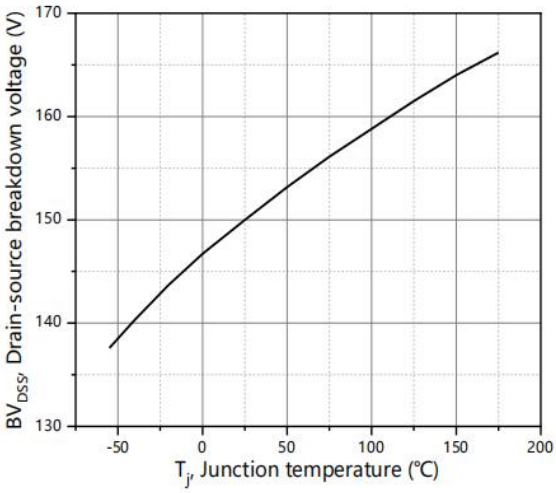


Figure 5. Drain-source breakdown voltage

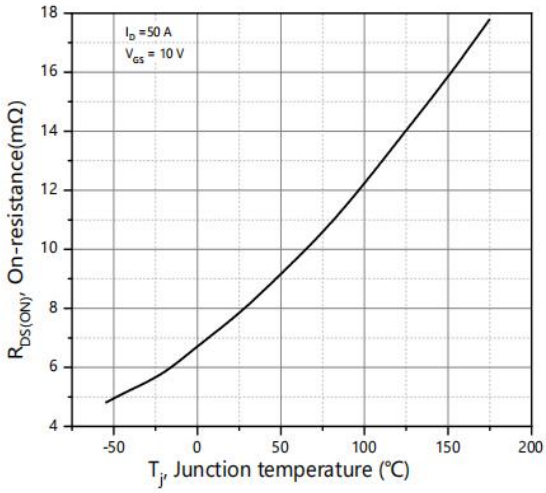


Figure 6. Drain-source on-state resistance

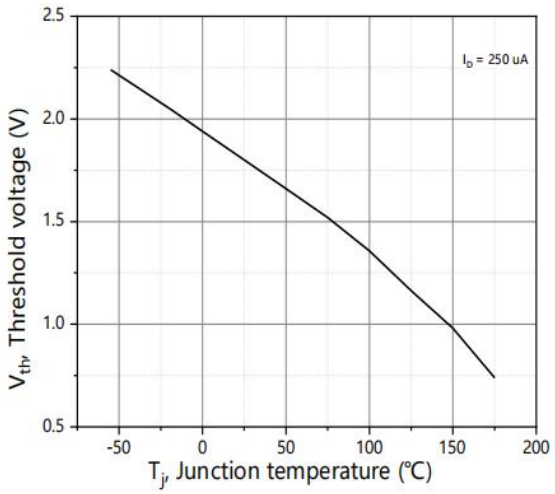


Figure 7. Threshold voltage

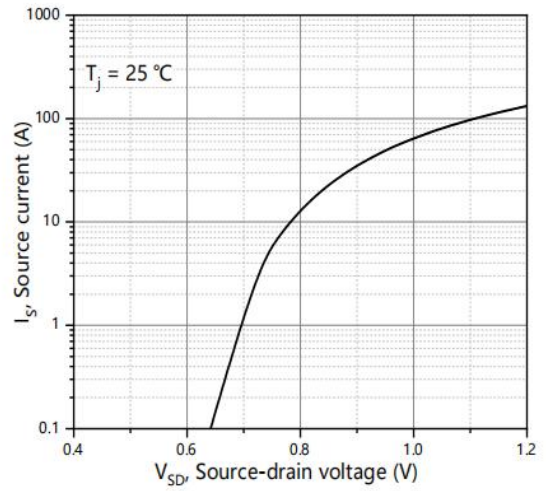


Figure 8. Forward characteristic of body diode

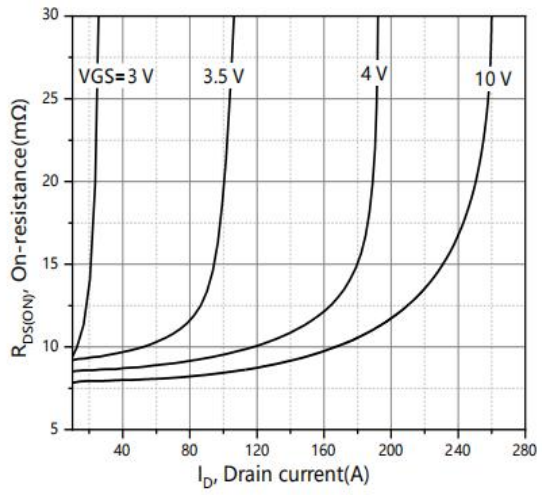


Figure 9. Drain-source on-state resistance

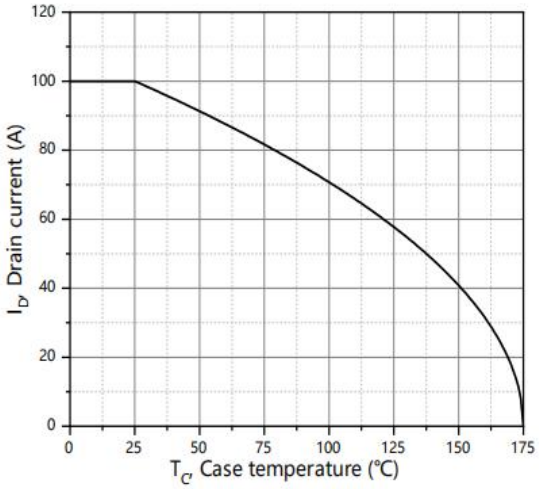


Figure 10. Drain current

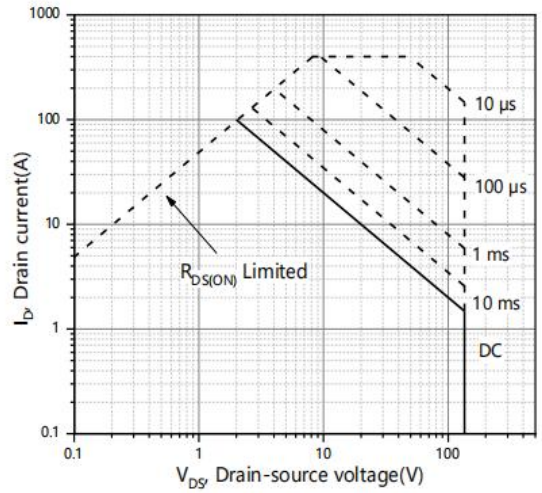


Figure 11. Safe operation area T_C=25℃

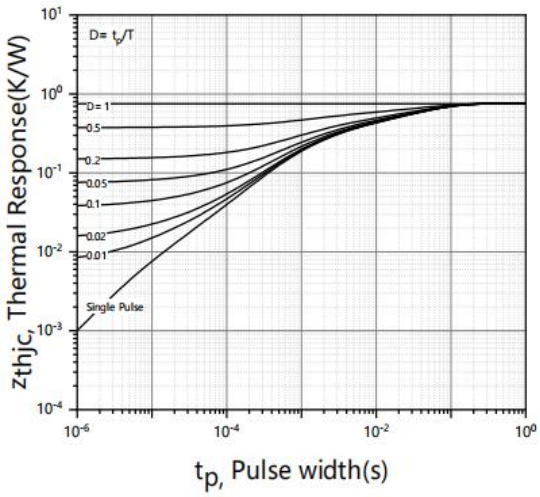


Figure 12. Max. transient thermal impedance

Test circuits and waveforms

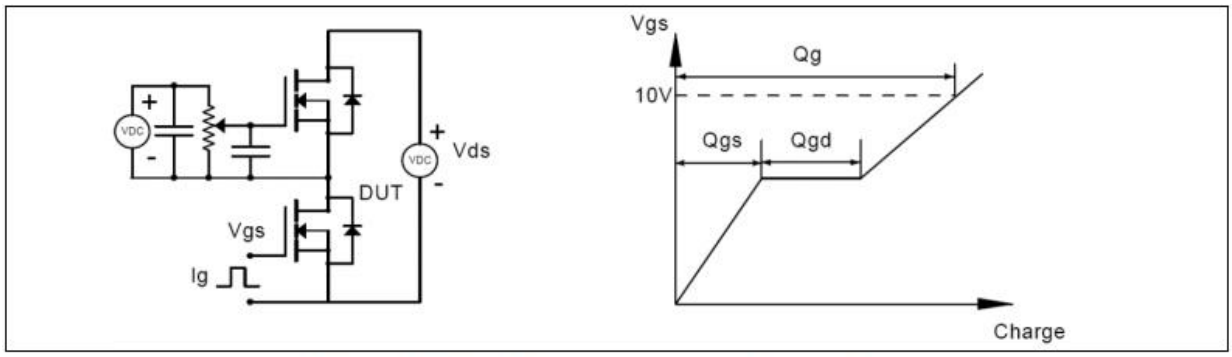


Figure 1. Gate charge test circuit & waveform

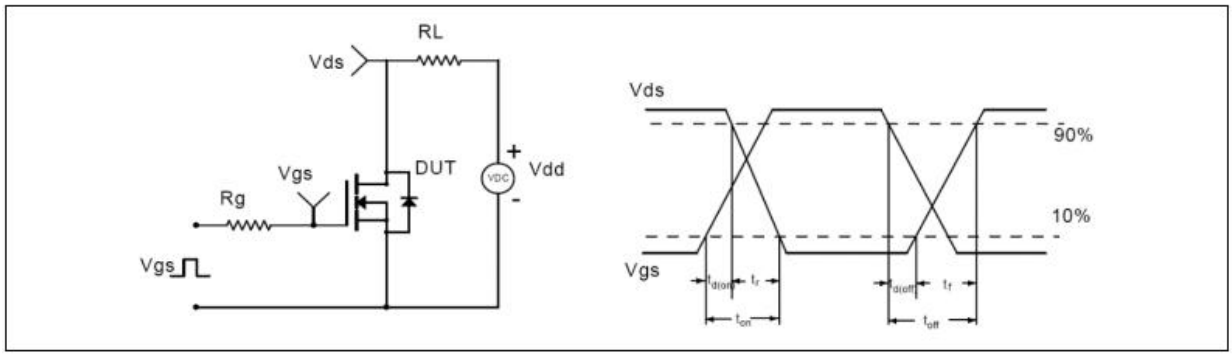


Figure 2. Switching time test circuit & waveforms

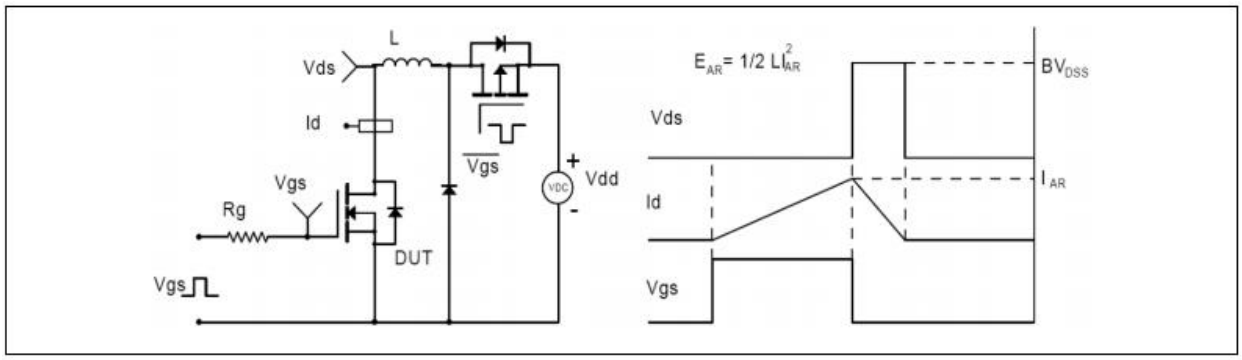


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

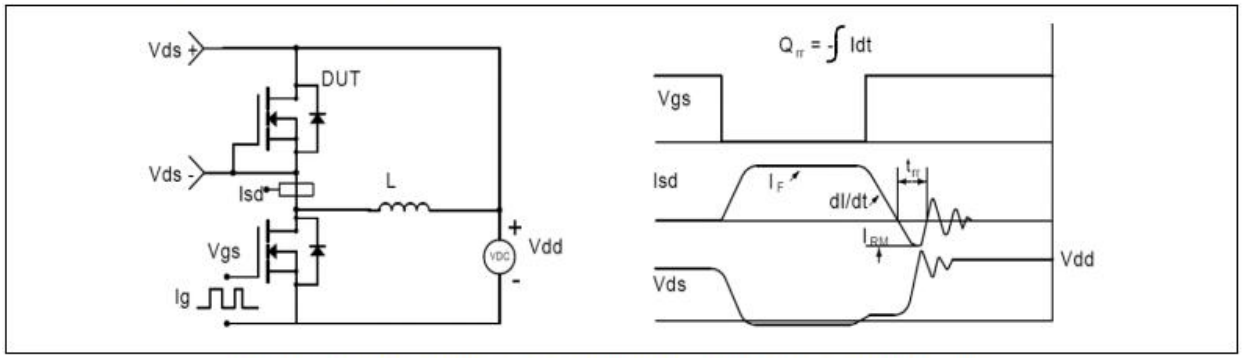
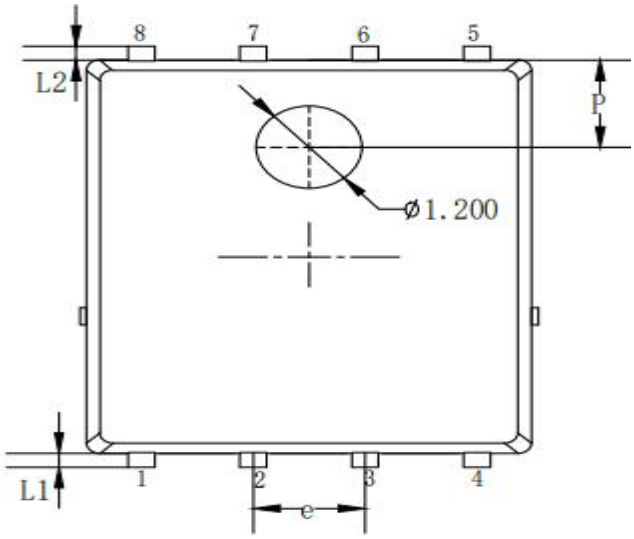
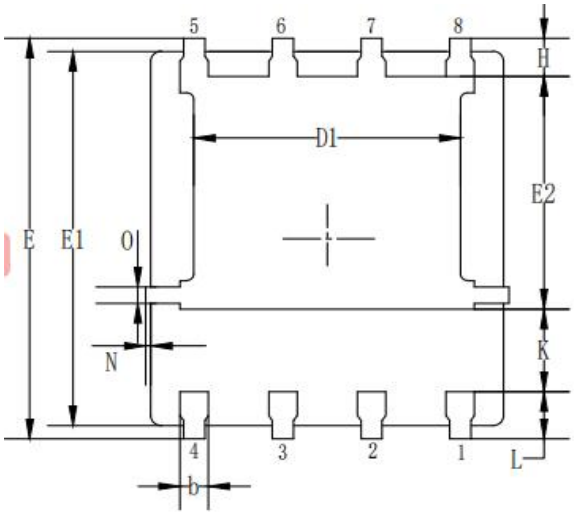
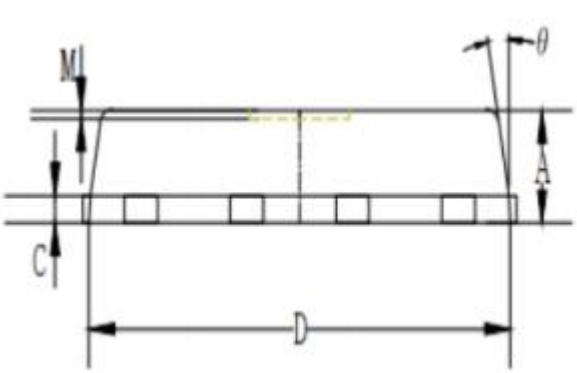


Figure 4. Diode reverse recovery test circuit & waveforms

Package Outline Dimensions







Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.10
D1	3.72	3.82	3.92
E	6.00	6.15	6.25
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.69	0.75
L1/L2	0.10 ~ 0.20		
θ	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		

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